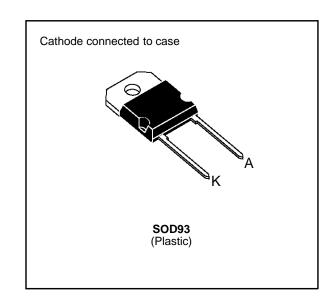


# BYT 30P-200 $\rightarrow$ 400

# **FAST RECOVERY RECTIFIER DIODES**

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING



#### **SUITABLE APPLICATIONS**

- FREE WHEELING DIODE IN CONVERTERS AND MOTOR CONTROL CIRCUITS
- RECTIFIER IN S.M.P.S.

#### **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Parameter		
I <sub>FRM</sub>	Repetive Peak Forward Current	urrent t <sub>p</sub> ≤ 10μs		Α
I <sub>F (RMS)</sub>	RMS Forward Current		50	Α
I <sub>F (AV)</sub>	Average Forward Current	$T_c = 100^{\circ}C$ $\delta = 0.5$	30	А
I <sub>FSM</sub>	Surge non Repetitive Forward Current	t <sub>p</sub> = 10ms Sinusoidal	350	А
Р	Power Dissipation	T <sub>c</sub> = 100°C	50	W
T <sub>stg</sub> T <sub>j</sub>	Storage and Junction Temperature Range		- 40 to + 150 - 40 to + 150	°C

Symbol	Parameter		BYT 30P-		
Cymbol	raidifictor	200	300	400	Unit
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	200	300	400	V
V <sub>RSM</sub>	Non Repetitive Peak Reverse Voltage	220	330	440	V

#### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R <sub>th (j-c)</sub>	Junction-case	1	°C/W

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#### **ELECTRICAL CHARACTERISTICS**

#### STATIC CHARACTERISTICS

Synbol	Test Conditions			Тур.	Max.	Unit
I <sub>R</sub>	T <sub>j</sub> = 25°C	$V_R = V_{RRM}$			35	μΑ
	T <sub>j</sub> = 100°C				6	mA
V <sub>F</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 30A			1.5	V
	T <sub>j</sub> = 100°C				1.4	

#### RECOVERY CHARACTERISTICS

Symbol		Test Conditions					Max.	Unit
t <sub>rr</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A	$di_F/dt = -15A/\mu s$	$V_R = 30V$			100	ns
		I <sub>F</sub> = 0.5A	$I_R = 1A$	$I_{rr} = 0.25A$			50	

### TURN-OFF SWITCHING CHARACTERISTICS (Without Series Inductance)

Symbol	Test Conditions			Тур.	Max.	Unit
t <sub>IRM</sub>	di <sub>F</sub> /dt = - 120A/μs	V <sub>CC</sub> = 200 V I <sub>F</sub> = 30A			75	ns
	$di_F/dt = -240A/\mu s$	$L_p \le 0.05 \mu H$ $T_j = 100^{\circ} C$ See figure 11		50		
I <sub>RM</sub>	di <sub>F</sub> /dt = -120A/μs				9	Α
	di <sub>F</sub> /dt = - 240A/μs			12		

## TURN-OFF OVERVOLTAGE COEFFICIENT (With Series Inductance)

Symbol	Test Conditions				Тур.	Max.	Unit
$C = \frac{V_{RP}}{V_{CC}}$	$T_j = 100^{\circ}C$ $di_F/dt = -30A/\mu s$	$V_{CC} = 60V$ $L_p = 1\mu H$	I <sub>F</sub> = I <sub>F (AV)</sub> See figure 12		3.3		

To evaluate the conduction losses use the following equations:

$$V_F = 1.1 + 0.0095 I_F$$
  $P = 1.1 \times I_{F(AV)} + 0.0095 I_{F^2(RMS)}$ 

Figure 1. Low frequency power losses versus average current

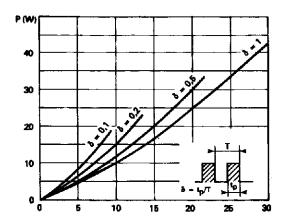


Figure 2. Peak current versus form factor

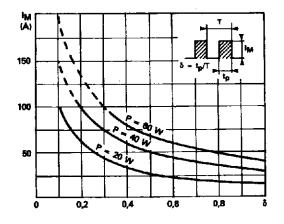


Figure 3. Non repetitive peak surge current versus overload duration

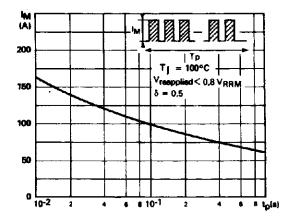


Figure 4. Thermal impedance versus pulse width

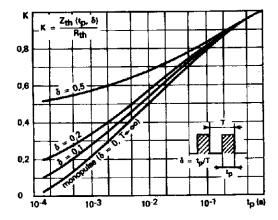


Figure 5. Voltage drop versus forward current

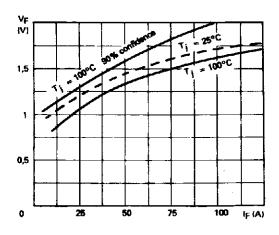


Figure 6. Recovery charge versus di<sub>F</sub>/d<sub>t-</sub>

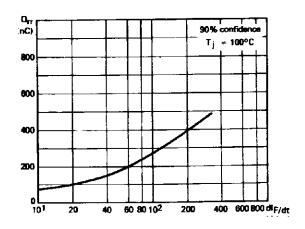


Figure 7. Recovery time versus di<sub>F</sub>/d<sub>t-</sub>

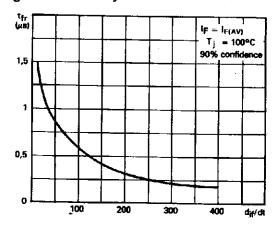


Figure 8. Peak reverse current versus dif/dt-

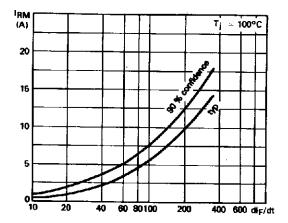


Figure 9. Peak forward voltage versus di<sub>F</sub>/d<sub>t-</sub>

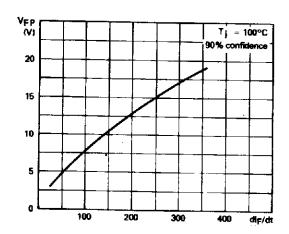


Figure 10. Dynamic parameters versus junction temperature.

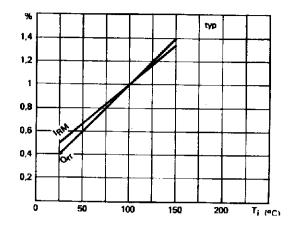


Figure 11. Turn-off switching characteristics (without series inductance).

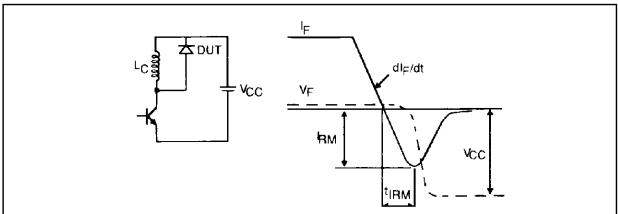
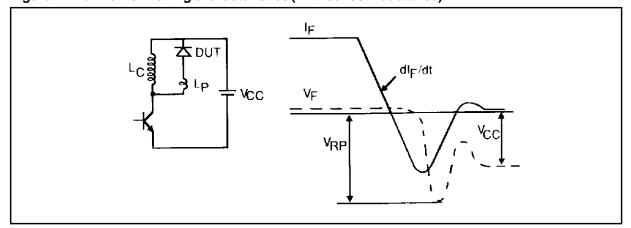
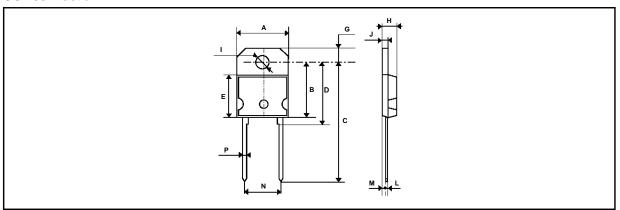


Figure 12. Turn-off switching characteristics (with series inductance)



#### **PACKAGE MECHANICAL DATA:**

SOD93 Plastic



	DIMENSIONS					
REF.	Millimeters		Inc	hes		
	Min.	Max.	Min.	Max.		
Α	14.7	15.2	0.578	0.596		
В		16.2		0.637		
С	31 typ		1.220 typ			
D	18 typ		0.708 typ			
E		12.2		0.480		
G	3.95	4.15	0.155	0.163		
Н	4.7	4.9	0.185	0.193		
I	4	4.1	0.157	0.161		
J	1.17	1.37	0.046	0.054		
L	0.5	0.78	0.019	0.030		
М	2.5 typ		0.098 typ			
N	10.8	11.1	0.425	0.437		
Р	1.1	1.3	0.043	0.051		

Cooling method: by conduction (method C) Marking: type number Weight: 4.3g Recommended torque value: 80cm. N

Maximum torque value: 100cm. N

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